

IN THE CLAIMS

Please amend Claim 10 to read as follows (a version of Claim 10 marked up to show the changes thereto is submitted herewith. All pending claims, whether amended or not, are reproduced below):

Sub G1
F1
7. (Previously Amended) A semiconductor device comprising a substrate and formed thereon an active layer having the surface^{1/2} of (111)-plane; the active layer being used in photoelectric conversion, where an angle formed by any arbitrary two cutting lines not coming into coincidence is represented by θ , and the active layer has a cutting angle of $|\cos\theta| = \frac{1}{2}$ or $3^{1/2}/2$.

9. (Previously Amended) The semiconductor device according to Claim 7, wherein the deviation of surface from the strict (111) plane is within an angle equal to $24/60$ ths of a degree ($0^\circ 24'$).

Sub G2
F2
10. (Amended) A photoelectric conversion element comprising an anti-reflection layer, silicon layers, and an electrode, provided from the light incident side^{1/2}, wherein all of the silicon layers are epitaxial silicon layers, and wherein the silicon layers comprise an n^+ layer and a p^- layer provided from the light incident side.